



GFS SERIES

6 to 30kV, 25mA, 100nS
Axial Lead Low Current Diodes



Features

- Low Power
- Miniature Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

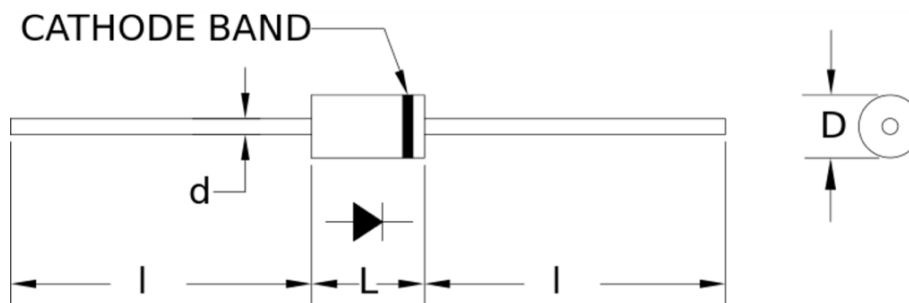
Specifications¹

Part Number	V _{RRM} V	I _{FAVM} mA	V _F V	I _R μA	I _{FSM} A	C _J pF	T _{RR} nS	L in.	D in.	d in.	l in.
G6FS	6000	25	18	0.2	3	0.38	100	0.32	0.12	0.020	1.0
G7FS	7000	25	18	0.2	3	0.38	100	0.32	0.12	0.020	1.0
G8FS	8000	25	23	0.2	3	0.65	100	0.32	0.12	0.024	1.0
G10FS	10000	25	23	0.2	3	0.65	100	0.32	0.12	0.024	1.0
G12FS	12000	25	25	0.2	3	0.26	100	0.40	0.12	0.024	1.0
G15FS	15000	25	25	0.2	3	0.26	100	0.40	0.12	0.024	1.0
G20FS	20000	25	35	0.2	3	0.25	100	0.47	0.12	0.024	1.0
G25FS	25000	25	42	0.2	3	0.20	100	0.47	0.12	0.024	1.0
G30FS	30000	25	48	0.2	3	0.26	100	0.47	0.12	0.024	1.0

Temperature °C	
Operating Temperature	-55 to 125
Storage Temperature	-55 to 175
Maximum Junction Temperature	125

¹125°C ambient temperature unless stated otherwise.

Drawings

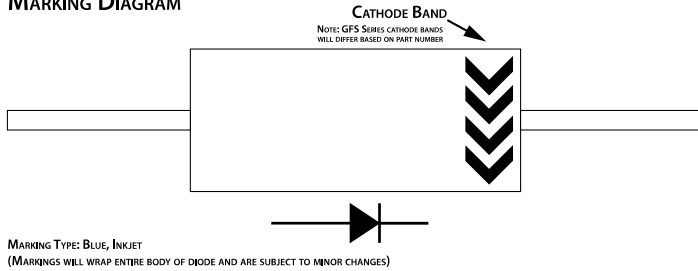


Dimensions in inches, tolerances ±0.020 except as noted



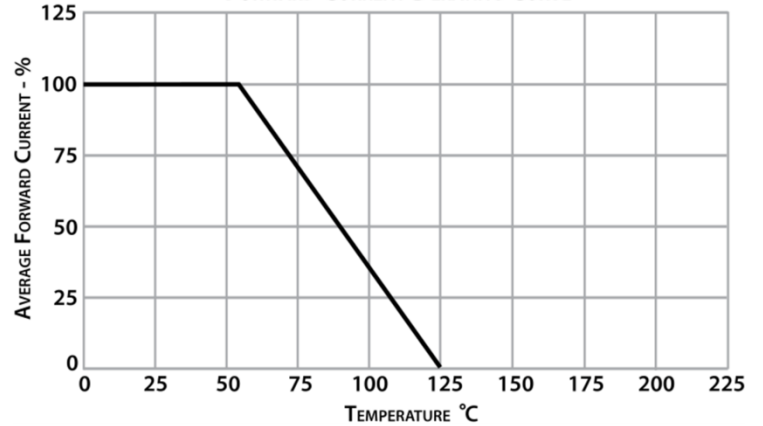
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MARKING DIAGRAM



MARKING TYPE: BLUE, INKJET
(MARKINGS WILL WRAP ENTIRE BODY OF DIODE AND ARE SUBJECT TO MINOR CHANGES)

FORWARD CURRENT DERATING CURVE



Specification Definitions

Specifications		Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At T _A = 55°C
V_F	Maximum Forward Voltage Drop	At 10mA
I_R	Maximum Leakage Current	At V _{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I _F = 0.5 I _{FAVM} ; I _R = -I _{FAVM} ; I _{RR} = -0.25 I _{FAVM}

Note: Specifications subject to change without notice. Photo is representation only.

